Cheol Seong Hwang

List of Publications by Year
in descending order

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		5782	7043
621	33,683	84	159
papers	citations	h-index	g-index

634	634	634	23532
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Review of Semiconductor Flash Memory Devices for Material and Process Issues. Advanced Materials, 2023, 35, e2200659.	11.1	42
2	Enhanced Ferroelectric Properties in Hf_{0.5}Zr_{0.5}O₂ Films Using a HfO_{0.61}N_{0.72} Interfacial Layer. Advanced Electronic Materials, 2022, 8, 2100042.	2.6	24
3	Atomic layer deposition of SnSe_x thin films using Sn(N(CH₃)₂)₄ and Se(Si(CH₃)₃)₂ with NH₃ co-injection. Dalton Transactions, 2022, 51, 594-601.	1.6	2
4	Cross-linked structure of self-aligned p-type SnS nanoplates for highly sensitive NO₂ detection at room temperature. Journal of Materials Chemistry A, 2022, 10, 4711-4719.	5.2	14
5	Negative Capacitance from the Inhomogenous Stray Field in a Ferroelectricâ€“Dielectric Structure. Advanced Functional Materials, 2022, 32, .	7.8	11
6	Reversible transition between the polar and antipolar phases and its implications for wake-up and fatigue in HfO2-based ferroelectric thin film. Nature Communications, 2022, 13, 645.	5.8	66
7	Improving the water-resistance of MgO-based metalâ€“insulatorâ€“metal capacitors by inserting a BeO thin film grown via atomic layer deposition. Journal of Materials Chemistry C, 2022, 10, 6611-6620.	2.7	1
8	Training Method for Accurate Offâ€Chip Training of Oneâ€Selectorâ€Oneâ€Resistor Crossbar Array with Nonlinearity and Wire Resistance. Advanced Intelligent Systems, 2022, 4, .	3.3	1
9	The fundamentals and applications of ferroelectric HfO2. Nature Reviews Materials, 2022, 7, 653-669.	23.3	162
10	Demonstration of Neuromodulationâ€inspired Stashing System for Energyâ€efficient Learning of Spiking Neural Network using a Selfâ€Rectifying Memristor Array. Advanced Functional Materials, 2022, 32, .	7.8	12
11	The Contrasting Impacts of the Al₂O₃ and Y₂O₃ Insertion Layers on the Crystallization of ZrO₂ Films for Dynamic Random Access Memory Capacitors. Advanced Electronic Materials, 2022, 8, .	2.6	4
12	Atomistic prediction on the composition- and configuration-dependent bandgap of Ga(As,Sb) using cluster expansion and ab initio thermodynamics. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2022, 280, 115713.	1.7	1
13	Enhanced Electrical Properties of an Al-Doped TiO₂ Dielectric Film on a TiN Electrode by Adopting an Atomic Layer Deposited Ru Interlayer. ACS Applied Electronic Materials, 2022, 4, 2005-2014.	2.0	2
14	Reliable Domainâ€Specific Exclusive Logic Gates Using Reconfigurable Sequential Logic Based on Antiparallel Bipolar Memristors. Advanced Intelligent Systems, 2022, 4, 2270021.	3.3	1
15	Memory Window Expansion for Ferroelectric FET based Multilevel NVM: Hybrid Solution with Combination of Polarization and Injected Charges. , 2022, , .		0
16	Oxygenâ€Scavenging Effects of Added Ti Layer in the TiN Gate of Metalâ€Ferroelectricâ€Insulatorâ€Semiconductor Capacitor with Alâ€Doped HfO₂ Ferroelectric Film. Advanced Electronic Materials, 2022, 8, .	2.6	13
17	Characterization of a 2D Electron Gas at the Interface of Atomicâ€Layer Deposited Al 2 O 3 /ZnO Thin Films for a Fieldâ€Effect Transistor. Advanced Electronic Materials, 2021, 7, 2000876.	2.6	8
18	Review of ferroelectric fieldâ€effect transistors for threeâ€dimensional storage applications. Nano Select, 2021, 2, 1187-1207.	1.9	27

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19	Atomistic prediction on the configuration- and temperature-dependent dielectric constant of Be_{0.25}Mg_{0.75}O superlattice as a high-Îdielectric layer. Journal of Materials Chemistry C, 2021, 9, 851-859.	2.7	7
20	Atomic layer deposition of chalcogenides for next-generation phase change memory. Journal of Materials Chemistry C, 2021, 9, 3708-3725.	2.7	23
21	Enhancement of electrical performance of atomic layer deposited SnO films via substrate surface engineering. Journal of Materials Chemistry C, 2021, 9, 12314-12321.	2.7	6
22	Polarizing and depolarizing charge injection through a thin dielectric layer in a ferroelectricâ€“dielectric bilayer. Nanoscale, 2021, 13, 2556-2572.	2.8	26
23	Comparison of high-k Y₂O₃/TiO₂ bilayer and Y-doped TiO₂ thin films on Ge substrate. Journal Physics D: Applied Physics, 2021, 54, 185110.	1.3	2
24	Atomistic Understanding of the Ferroelectric Properties of a Wurtziteâ€Structure (AlN)_n/(ScN)_m Superlattice. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100009.	1.2	14
25	Improved Properties of the Atomic Layer Deposited Ru Electrode for Dynamic Random-Access Memory Capacitor Using Discrete Feeding Method. ACS Applied Materials & Interfaces, 2021, 13, 23915-23927.	4.0	7
26	A Highâ€Speed True Random Number Generator Based on a Cu_xTe_{1â^'x} Diffusive Memristor. Advanced Intelligent Systems, 2021, 3, 2100062.	3.3	21
27	Threshold Voltage Modulation in a Transistor with a Two-Dimensional Electron Gas Channel at the Interface between Al₂O₃ and Sub-5 nm ZnO Films. ACS Applied Electronic Materials, 2021, 3, 3247-3255.	2.0	7
28	A Highâ€Speed True Random Number Generator Based on a Cu_xTe_{1â^'x} Diffusive Memristor. Advanced Intelligent Systems, 2021, 3, 2170057.	3.3	1
29	Inâ€Memory Stateful Logic Computing Using Memristors: Gate, Calculation, and Application. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2100208.	1.2	25
30	Area-Type Electronic Bipolar Switching Al/TiO_{1.7}/TiO₂/Al Memory with Linear Potentiation and Depression Characteristics. ACS Applied Materials & Interfaces, 2021, 13, 39561-39572.	4.0	10
31	Improved ferroelectricity in Hf0.5Zr0.5O2 by inserting an upper HfOxNy interfacial layer. Applied Physics Letters, 2021, 119, .	1.5	8
32	Time-varying data processing with nonvolatile memristor-based temporal kernel. Nature Communications, 2021, 12, 5727.	5.8	42
33	InterPhon: Ab initio interface phonon calculations within a 3D electronic structure framework. Computer Physics Communications, 2021, 268, 108089.	3.0	0
34	eWB: Event-Based Weight Binarization Algorithm for Spiking Neural Networks. IEEE Access, 2021, 9, 38097-38106.	2.6	4
35	Investigating the Reasons for the Difficult Erase Operation of a Chargeâ€Trap Flash Memory Device with Amorphous Oxide Semiconductor Thinâ€Film Channel Layers. Physica Status Solidi - Rapid Research Letters, 2021, 15, 2000549.	1.2	13
36	Trap Reduction through O 3 Postâ€Deposition Treatment of Y 2 O 3 Thin Films Grown by Atomic Layer Deposition on Ge Substrates. Advanced Electronic Materials, 2021, 7, 2000819.	2.6	3

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37	Optimized Al-doped TiO₂ gate insulator for a metal-oxide-semiconductor capacitor on a Ge substrate. Journal of Materials Chemistry C, 2021, 9, 1572-1583.	2.7	6
38	Influences of oxygen source and substrate temperature on the unusual growth mechanism of atomic layer deposited magnesium oxide using bis(cyclopentadienyl)magnesium precursor. Journal of Materials Chemistry C, 2021, 9, 15359-15374.	2.7	4
39	Effect of local strain energy to predict accurate phase diagram of IIIâ€“V pseudobinary systems: case of Ga(As,Sb) and (In,Ga)As. Journal Physics D: Applied Physics, 2021, 54, 045104.	1.3	4
40	A new sensing mechanism of Si FET-based gas sensor using pre-bias. Sensors and Actuators B: Chemical, 2020, 302, 127147.	4.0	10
41	X-ray spectroscopy study on the electronic structure of Sn-added p-type SnO films. Journal of Physics Condensed Matter, 2020, 32, 065502.	0.7	10
42	Initial oxidation and surface stability diagram of Ge(100) as a function of the temperature and oxygen partial pressure through ab initio thermodynamics. Physica Scripta, 2020, 95, 025701.	1.2	0
43	Atomic engineering of metastable BeO6 octahedra in a rocksalt framework. Applied Surface Science, 2020, 501, 144280.	3.1	8
44	A Stateful Logic Family Based on a New Logic Primitive Circuit Composed of Two Antiparallel Bipolar Memristors. Advanced Intelligent Systems, 2020, 2, 1900082.	3.3	36
45	Kernel Application of the Stacked Crossbar Array Composed of Selfâ€Rectifying Resistive Switching Memory for Convolutional Neural Networks. Advanced Intelligent Systems, 2020, 2, 1900116.	3.3	11
46	Bipolar resistive switching property of Si₃N_{4â^'x}thin films depending on N deficiency. Journal of Materials Chemistry C, 2020, 8, 1755-1761.	2.7	4
47	Fieldâ€Induced Ferroelectric Hf_{1â€‹}_xZr_xO₂ Thin Films for Highâ€‹k Dynamic Random Access Memory. Advanced Electronic Materials, 2020, 6, 2000631.	2.6	19
48	Substrate Surface Modification for Enlarging Two-Dimensional SnS Grains at Low Temperatures. Chemistry of Materials, 2020, 32, 9026-9033.	3.2	9
49	Study of ferroelectric characteristics of Hf0.5Zr0.5O2 thin films grown on sputtered or atomic-layer-deposited TiN bottom electrodes. Applied Physics Letters, 2020, 117, .	1.5	19
50	Impact of the Atomic Layer-Deposited Ru Electrode Surface Morphology on Resistive Switching Properties of TaO_x-Based Memory Structures. ACS Applied Materials & Interfaces, 2020, 12, 55331-55341.	4.0	14
51	Substrate-Dependent Growth Behavior of Atomic-Layer-Deposited Zinc Oxide and Zinc Tin Oxide Thin Films for Thin-Film Transistor Applications. Journal of Physical Chemistry C, 2020, 124, 26780-26792.	1.5	12
52	Highly sensitive flexible NO₂ sensor composed of vertically aligned 2D SnS₂ operating at room temperature. Journal of Materials Chemistry C, 2020, 8, 11874-11881.	2.7	38
53	Comparative Study on the Gateâ€Induced Electrical Instability of pâ€Type SnO Thinâ€Film Transistors with SiO₂ and Al₂O₃/SiO₂ Gate Dielectrics. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000304.	1.2	1
54	Radical-Enhanced Atomic Layer Deposition of a Tungsten Oxide Film with the Tunable Oxygen Vacancy Concentration. Journal of Physical Chemistry C, 2020, 124, 18156-18164.	1.5	14

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55	Complementary Resistive Switching and Synaptic-Like Memory Behavior in an Epitaxial SrFeO_{2.5} Thin Film through Oriented Oxygen-Vacancy Channels. ACS Applied Materials & Interfaces, 2020, 12, 41740-41748.	4.0	36
56	Origin of the Threshold Voltage Shift in a Transistor with a 2D Electron Gas Channel at the Al 2 O 3 /SrTiO 3 Interface. Advanced Electronic Materials, 2020, 6, 1901286.	2.6	8
57	Areaâ€Type Electronic Bipolar Resistive Switching of Pt/Al 2 O 3 /Si 3 N 3.0 /Ti with Formingâ€Free, Selfâ€Rectification, and Nonlinear Characteristics. Physica Status Solidi - Rapid Research Letters, 2020, 14, 2000209.	1.2	9
58	Atomic Layer Deposition of SnTe Thin Film Using Sn(N(CH₃)₂)₄ and Te(Si(CH₃)₃)₂ with Ammonia Coinjection. Crystal Growth and Design, 2020, 20, 4649-4656.	1.4	5
59	Resistive random access memory based on gallium oxide thin films for self-powered pressure sensor systems. Ceramics International, 2020, 46, 21141-21148.	2.3	14
60	Ferroelectric domain wall memory with embedded selector realized in LiNbO3 single crystals integrated on Si wafers. Nature Materials, 2020, 19, 1188-1194.	13.3	92
61	An ab initio approach on the asymmetric stacking of GaAs â€˜111â€™ nanowires grown by a vaporâ€“solid method. Nanoscale, 2020, 12, 17703-17714.	2.8	6
62	Review of defect chemistry in fluorite-structure ferroelectrics for future electronic devices. Journal of Materials Chemistry C, 2020, 8, 10526-10550.	2.7	94
63	A Combination of a Volatileâ€Memristorâ€Based True Randomâ€Number Generator and a Nonlinearâ€Feedback Shift Register for Highâ€Speed Encryption. Advanced Electronic Materials, 2020, 6, 1901117.	2.6	22
64	Cation-Regulated Transformation for Continuous Two-Dimensional Tin Monosulfide. Chemistry of Materials, 2020, 32, 2313-2320.	3.2	21
65	Investigation of the electronic structure of amorphous SnO film using x-ray absorption spectroscopy. Applied Physics Letters, 2020, 116, 052102.	1.5	1
66	Electroforming-Free, Flexible, and Reliable Resistive Random-Access Memory Based on an Ultrathin TaO_x Film. ACS Applied Materials & Interfaces, 2020, 12, 10681-10688.	4.0	26
67	Resistive switching materials forÂinformation processing. Nature Reviews Materials, 2020, 5, 173-195.	23.3	668
68	Modulated filamentary conduction of Ag/TiO2 core-shell nanowires to impart extremely sustained resistance switching behavior in a flexible composite. Applied Materials Today, 2020, 19, 100569.	2.3	12
69	Atomic Layer Deposition of Ge_xSe_{1â€“x} Thin Films for Endurable Ovonic Threshold Selectors with a Low Threshold Voltage. ACS Applied Materials & Interfaces, 2020, 12, 23110-23118.	4.0	19
70	Atomic layer deposition of Ru thin films using (2,4-dimethyloxopentadienyl)(ethylcyclopentadienyl)Ru and the effect of ammonia treatment during the deposition. Journal of Materials Chemistry C, 2020, 8, 6993-7004.	2.7	17
71	A Comparative Study on the Ferroelectric Performances in Atomic Layer Deposited Hf0.5Zr0.5O2 Thin Films Using Tetrakis(ethylmethylamino) and Tetrakis(dimethylamino) Precursors. Nanoscale Research Letters, 2020, 15, 72.	3.1	38
72	Novel Applications of Antiferroelectrics and Relaxor Ferroelectrics: A Materialâ€™s Point of View. Topics in Applied Physics, 2020, , 343-357.	0.4	2

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73	A first-principles study of the structural and electronic properties of the epitaxial Ge(1â€‰1â€‰1)/La₂O₃(0â€‰0â€‰1) heterostructure. Journal Physics D: Applied Physics, 2019, 52, 365101.	2.8	9
74	Scaling the Equivalent Oxide Thickness by Employing a TiO₂ Thin Film on a ZrO₂â€“Al₂O₃â€Based Dielectric for Further Scaling of Dynamic Random Access Memory. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900282.	1.2	9
75	Memristor crossbar array for binarized neural networks. AIP Advances, 2019, 9, .	0.6	21
76	Leakage Current Control of SrTiO₃ Thin Films through Al Doping at the Interface between Dielectric and Electrode Layers via Atomic Layer Deposition. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900373.	1.2	5
77	Electrically-generated memristor based on inkjet printed silver nanoparticles. Nanoscale Advances, 2019, 1, 2990-2998.	2.2	22
78	Atomic Layer Deposition of Nanocrystalline-As-Deposited (GeTe)_x(Sb₂Te₃)_{1â€“x} Films for Endurable Phase Change Memory. Chemistry of Materials, 2019, 31, 8752-8763.	3.2	15
79	A First-Principles Study on the Oxygen Adsorption and Interface Characteristics with a-GeO2 of Ge[001] Nanowire. Journal of the Korean Physical Society, 2019, 75, 283-287.	0.3	0
80	Fluorite-structure antiferroelectrics. Reports on Progress in Physics, 2019, 82, 124502.	8.1	47
81	A comprehensive study on the mechanism of ferroelectric phase formation in hafnia-zirconia nanolaminates and superlattices. Applied Physics Reviews, 2019, 6, .	5.5	73
82	Theoretical understanding of the catalyst-free growth mechanism of GaAs <111>B nanowires. Applied Surface Science, 2019, 497, 143740.	3.1	7
83	Ferroelectric switching in bilayer 3R MoS2 via interlayer shear mode driven by nonlinear phononics. Scientific Reports, 2019, 9, 14919.	1.6	19
84	Atomic layer deposition of Ta-doped SnO2 films with enhanced dopant distribution for thermally stable capacitor electrode applications. Applied Surface Science, 2019, 497, 143804.	3.1	11
85	Substrate Effects on the Growth Behavior of Atomic-Layer-Deposited Ru Thin Films Using RuO₄ Precursor and N₂/H₂ Mixed Gas. Journal of Physical Chemistry C, 2019, 123, 22539-22549.	1.5	8
86	Understanding ferroelectric phase formation in doped HfO₂ thin films based on classical nucleation theory. Nanoscale, 2019, 11, 19477-19487.	2.8	55
87	VCAM: Variation Compensation through Activation Matching for Analog Binarized Neural Networks. , 2019, , .		7
88	Developing Precursor Chemistry for Atomic Layer Deposition of High-Density, Conformal GeTe Films for Phase-Change Memory. Chemistry of Materials, 2019, 31, 8663-8672.	3.2	12
89	Electroforming-Free Bipolar Resistive Switching in GeSe Thin Films with a Ti-Containing Electrode. ACS Applied Materials & Interfaces, 2019, 11, 38910-38920.	4.0	13
90	Effect of the Annealing Temperature of the Seed Layer on the Following Main Layer in Atomicâ€Layerâ€Deposited SrTiO 3 Thin Films. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800557.	1.2	3

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91	Novel Selectorâ€Induced Currentâ€Limiting Effect through Asymmetry Control for Highâ€Density Oneâ€Selectorâ€“Oneâ€Resistor Crossbar Arrays. Advanced Electronic Materials, 2019, 5, 1800806.	2.6	10
92	Reduction of the Hysteresis Voltage in Atomicâ€Layerâ€Deposited pâ€Type SnO Thinâ€Film Transistors by Adopting an Al₂O₃ Interfacial Layer. Advanced Electronic Materials, 2019, 5, 1900371.	2.6	23
93	Ferroelectric memories. , 2019, , 393-441.		10
94	Modeling of Negative Capacitance in Ferroelectric Thin Films. Advanced Materials, 2019, 31, e1805266.	11.1	101
95	Stochastic Learning with Back Propagation. , 2019, , .		2
96	Matrix Mapping on Crossbar Memory Arrays with Resistive Interconnects and Its Use in In-Memory Compression of Biosignals. Micromachines, 2019, 10, 306.	1.4	16
97	Effect of Electrode Material on the Crystallization of GeTe Grown by Atomic Layer Deposition for Phase Change Random Access Memory. Micromachines, 2019, 10, 281.	1.4	8
98	Role of the Shortâ€Range Order in Amorphous Oxide on MoS₂/aâ€SiO₂ and MoS₂/aâ€HfO₂ Interfaces. Physica Status Solidi (B): Basic Research, 2019, 256, 1900002.	0.7	3
99	Broad Phase Transition of Fluoriteâ€Structured Ferroelectrics for Large Electrocaloric Effect. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900177.	1.2	8
100	Orientation-dependent structural and electronic properties of Ge/a-GeO₂ interfaces: first-principles study. Journal Physics D: Applied Physics, 2019, 52, 155101.	1.3	4
101	Tunneling Properties of the Charge Carriers through Sub-2-nm-Thick Oxide in Ge/a - GeO2/Ge Structures Using the First-Principles Scattering-State Method. Physical Review Applied, 2019, 11, .	1.5	3
102	Transient Negative Capacitance Effect in Atomicâ€Layerâ€Deposited Al₂O₃/Hf_{0.3}Zr_{0.7}O₂ Bilayer Thin Film. Advanced Functional Materials, 2019, 29, 1808228.	7.8	47
103	Impact of Zr Content in Atomic Layer Deposited Hf1âˆ'Zr O2 Thin Films. , 2019, , 75-101.		5
104	Impact of Electrodes on the Ferroelectric Properties. , 2019, , 341-364.		3
105	Effect of Surface/Interface Energy and Stress on the Ferroelectric Properties. , 2019, , 145-172.		5
106	Pyroelectric and Electrocaloric Effects and Their Applications. , 2019, , 217-244.		2
107	Negative Capacitance in HfO2- and ZrO2-Based Ferroelectrics. , 2019, , 473-493.		4
108	Artificial Neural Network for Response Inference of a Nonvolatile Resistance-Switch Array. Micromachines, 2019, 10, 219.	1.4	1

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109	High-Performance Thin-Film Transistors of Quaternary Indiumâ€“Zincâ€“Tin Oxide Films Grown by Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2019, 11, 14892-14901.	4.0	48
110	Markov Chain Hebbian Learning Algorithm With Ternary Synaptic Units. IEEE Access, 2019, 7, 10208-10223.	2.6	4
111	Timeâ€Efficient Stateful Dualâ€Bitâ€Memristor Logic. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900033.	1.2	17
112	Equilibrium crystal shape of GaAs and InAs considering surface vibration and new (111)B reconstruction: ab-initio thermodynamics. Scientific Reports, 2019, 9, 1127.	1.6	16
113	What Will Come After Vâ€NANDâ€”Vertical Resistive Switching Memory?. Advanced Electronic Materials, 2019, 5, 1800914.	2.6	61
114	Optical control of the layer degree of freedom through Wannierâ€“Stark states in polar 3R MoS₂. Journal of Physics Condensed Matter, 2019, 31, 315502.	0.7	5
115	Synthesis of Large Area Two-Dimensional MoS₂ Films by Sulfurization of Atomic Layer Deposited MoO₃ Thin Film for Nanoelectronic Applications. ACS Applied Nano Materials, 2019, 2, 7521-7531.	2.4	34
116	Defect-Engineered Electroforming-Free Analog HfO_x Memristor and Its Application to the Neural Network. ACS Applied Materials & Interfaces, 2019, 11, 47063-47072.	4.0	33
117	Temperature controlled Ru and RuO2 growth via O* radical-enhanced atomic layer deposition with Ru(EtCp)2. Journal of Chemical Physics, 2019, 151, 204701.	1.2	18
118	Singleâ€Cell Stateful Logic Using a Dualâ€Bit Memristor. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800629.	1.2	23
119	Nucleationâ€Limited Ferroelectric Orthorhombic Phase Formation in Hf_{0.5}Zr_{0.5}O₂ Thin Films. Advanced Electronic Materials, 2019, 5, 1800436.	2.6	55
120	Thermodynamic and Kinetic Origins of Ferroelectricity in Fluorite Structure Oxides. Advanced Electronic Materials, 2019, 5, 1800522.	2.6	128
121	Fabrication of a Cuâ€Coneâ€Shaped Cation Source Inserted Conductive Bridge Random Access Memory and Its Improved Switching Reliability. Advanced Functional Materials, 2019, 29, 1806278.	7.8	51
122	Mitigating wakeup effect and improving endurance of ferroelectric HfO2-ZrO2 thin films by careful La-doping. Journal of Applied Physics, 2019, 125, .	1.1	110
123	2D Electron Gas at the Interface of Atomicâ€Layerâ€Deposited Al₂O₃/TiO₂ on SrTiO₃ Single Crystal Substrate. Advanced Electronic Materials, 2019, 5, 1800527.	2.6	18
124	A True Random Number Generator Using Thresholdâ€Switchingâ€Based Memristors in an Efficient Circuit Design. Advanced Electronic Materials, 2019, 5, 1800543.	2.6	32
125	Controlling the Electrical Characteristics of ZrO₂/Al₂O₃/ZrO₂ Capacitors by Adopting a Ru Top Electrode Grown via Atomic Layer Deposition. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1800454.	1.2	23
126	Quantitative Analysis of the Incorporation Behaviors of Sr and Ti Atoms During the Atomic Layer Deposition of SrTiO₃ Thin Films. ACS Applied Materials & Interfaces, 2018, 10, 8836-8844.	4.0	15

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127	In₂Ga₂ZnO₇oxide semiconductor based charge trap device for NAND flash memory. Nanotechnology, 2018, 29, 155203.	1.3	26
128	Nonvolatile Memory Materials for Neuromorphic Intelligent Machines. Advanced Materials, 2018, 30, e1704729.	11.1	187
129	Chemical interactions in the atomic layer deposition of Geâ€“Sbâ€“Seâ€“Te films and their ovonic threshold switching behavior. Journal of Materials Chemistry C, 2018, 6, 5025-5032.	2.7	33
130	An artificial nociceptor based on a diffusive memristor. Nature Communications, 2018, 9, 417.	5.8	295
131	Improved Ferroelectric Switching Endurance of La-Doped Hf_{0.5}Zr_{0.5}O₂ Thin Films. ACS Applied Materials & Interfaces, 2018, 10, 2701-2708.	4.0	207
132	Highly Flexible Resistive Switching Memory Based on the Electronic Switching Mechanism in the Al/TiO₂/Al/Polyimide Structure. ACS Applied Materials & Interfaces, 2018, 10, 1828-1835.	4.0	68
133	Composition, Microstructure, and Electrical Performance of Sputtered SnO Thin Films for p-Type Oxide Semiconductor. ACS Applied Materials & Interfaces, 2018, 10, 3810-3821.	4.0	16
134	Nociceptive Memristor. Advanced Materials, 2018, 30, 1704320.	11.1	116
135	Demonstrating the Ultrathin Metalâ€“Insulatorâ€“ Metal Diode Using TiN/ZrO₂â€“Al₂O₃â€“ZrO₂Stack by Employing RuO₂Top Electrode. IEEE Transactions on Electron Devices, 2018, 65, 660-666.	1.6	17
136	Understanding the formation of the metastable ferroelectric phase in hafniaâ€“zirconia solid solution thin films. Nanoscale, 2018, 10, 716-725.	2.8	159
137	Temporary formation of highly conducting domain walls for non-destructive read-out of ferroelectric domain-wall resistance switching memories. Nature Materials, 2018, 17, 49-56.	13.3	188
138	MoO₂ as a thermally stable oxide electrode for dynamic random-access memory capacitors. Journal of Materials Chemistry C, 2018, 6, 13250-13256.	2.7	18
139	Morphotropic Phase Boundary of Hf_{1â€“x}Zr_xO₂ Thin Films for Dynamic Random Access Memories. ACS Applied Materials & Interfaces, 2018, 10, 42666-42673.	4.0	68
140	Effect of Growth Temperature during the Atomic Layer Deposition of the SrTiO₃ Seed Layer on the Properties of RuO₂/SrTiO₃/Ru Capacitors for Dynamic Random Access Memory Applications. ACS Applied Materials & Interfaces, 2018, 10, 41544-41551.	4.0	13
141	Dispersion in Ferroelectric Switching Performance of Polycrystalline Hf_{0.5}Zr_{0.5}O₂ Thin Films. ACS Applied Materials & Interfaces, 2018, 10, 35374-35384.	4.0	55
142	Diode Property and Positive Temperature Coefficient of Resistance of Pt/Al₂O₃/Nb:SrTiO₃. Advanced Electronic Materials, 2018, 4, 1800388.	2.6	7
143	La-doped Hf0.5Zr0.5O2 thin films for high-efficiency electrostatic supercapacitors. Applied Physics Letters, 2018, 113, .	1.5	43
144	Atomic Layer Deposited Oxygenâ€Deficient TaO_x Layers for Electroformingâ€Free and Reliable Resistance Switching Memory. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800429.	1.2	18

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145	Review and perspective on ferroelectric HfO2-based thin films for memory applications. MRS Communications, 2018, 8, 795-808.	0.8	360
146	Cu cone inserted CBRAM device fabrication and its improved switching reliability induced by field concentration effect. , 2018, , .		0
147	Investigation of the retention performance of an ultra-thin HfO2 resistance switching layer in an integrated memory device. Journal of Applied Physics, 2018, 124, .	1.1	24
148	Advanced memoryâ€"Materials for a new era of information technology. MRS Bulletin, 2018, 43, 330-333.	1.7	22
149	Electrical Properties of ZrO₂/Al₂O₃/ZrO₂â€Based Capacitors with TiN, Ru, and TiN/Ru Top Electrode Materials. Physica Status Solidi - Rapid Research Letters, 2018, 12, 1800356.	1.2	16
150	Atomic layer deposition(ALD) of Ru thin film on Ta<inf>2</inf>O<inf>5</inf>/Si substrate using RuO<inf>4</inf> precursor and H<inf>2</inf> gas. , 2018, , .		0
151	Understanding the Coexistence of Two Bipolar Resistive Switching Modes with Opposite Polarity in Pt/TiO₂/Ti/Pt Nanosized ReRAM Devices. ACS Applied Materials & Interfaces, 2018, 10, 29766-29778.	4.0	71
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